

ZXTP2012A

60V PNP LOW SATURATION MEDIUM POWER TRANSISTOR IN E-LINE

SUMMARY

$BV_{CEO} = -60V$; $R_{SAT} = 38m\Omega$; $I_C = -3.5A$

DESCRIPTION

Packaged in the E-line outline this new low saturation 60V PNP transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.

FEATURES

- 3.5 amps continuous current
- Up to 15 amps peak current
- Very low saturation voltages
- Excellent gain up to 10 amps

APPLICATIONS

- DC - DC converters
- MOSFET gate drivers
- Power switches
- Motor control

ORDERING INFORMATION

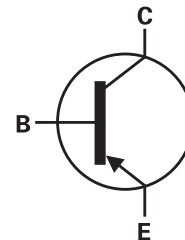
DEVICE	QUANTITY PER REEL
ZXTP2012ASTOA	2,000 units / reel
ZXTP2012ASTZ	2,000 units / carton

DEVICE MARKING

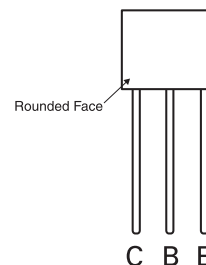
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E-line



PINOUT



TOP VIEW

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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Collector-base voltage	BV_{CBO}	-100	V
Collector-emitter voltage	BV_{CEO}	-60	V
Emitter-base voltage	BV_{EBO}	-7	V
Continuous collector current ^(a)	I_C	-3.5	A
Peak pulse current	I_{CM}	-15	A
Practical power dissipation at $T_A = 25^\circ\text{C}$ ^(a)	P_D	1.0	W
Linear derating factor		8	mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ ^(b)	P_D	0.71	W
Linear derating factor		5.7	mW/°C
Operating and storage temperature range	T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to ambient ^(a)	$R_{\theta JA}$	125	°C/W
Junction to ambient ^(b)	$R_{\theta JA}$	175	°C/W

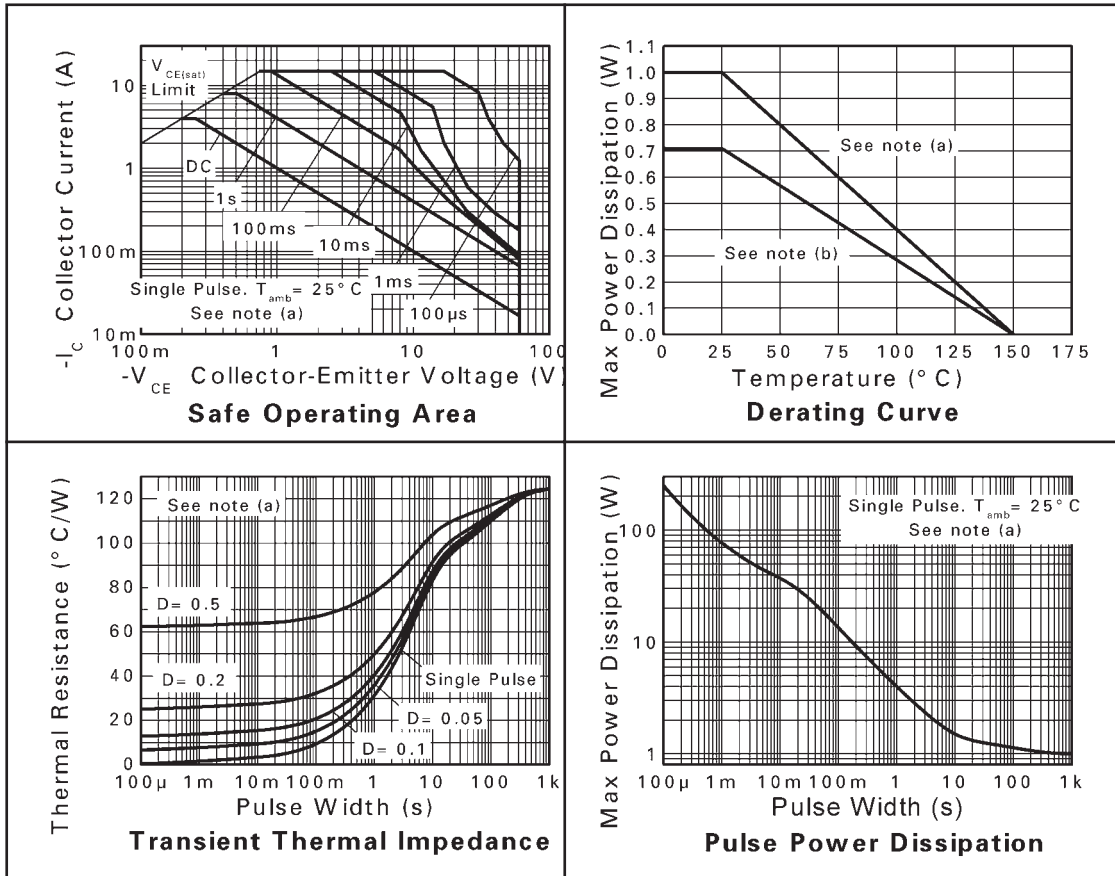
NOTES

(a) For a device through hole mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions. Collector lead length to solder point 4mm.

(b) For a device mounted in a socket in still air conditions. Collector lead length 10mm.

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CHARACTERISTICS



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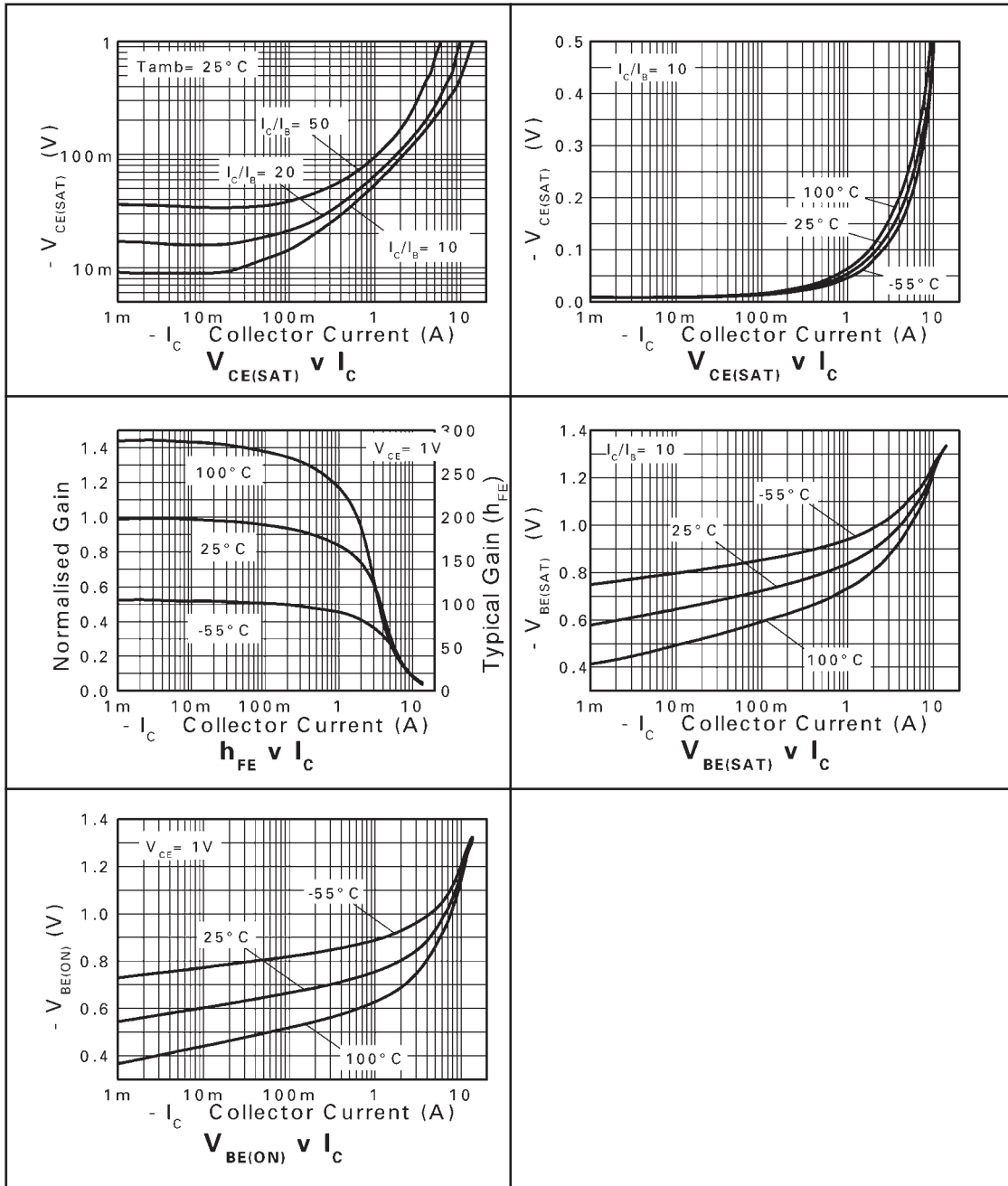
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Collector-base breakdown voltage	BV_{CBO}	-100	-120		V	$I_C = -100\mu\text{A}$
Collector-emitter breakdown voltage	BV_{CER}	-100	-120		V	$I_C = -1\mu\text{A}$, $R_B \leq 1\text{k}\Omega$
Collector-emitter breakdown voltage	BV_{CEO}	-60	-80		V	$I_C = -10\text{mA}^*$
Emitter-base breakdown voltage	BV_{EBO}	-7	-8.1		V	$I_E = -100\mu\text{A}$
Collector cut-off current	I_{CBO}		<1	-20 -0.5	nA μA	$V_{CB} = -80\text{V}$ $V_{CB} = -80\text{V}$, $T_{amb} = 100^{\circ}\text{C}$
Collector cut-off current	I_{CER} $R \leq 1\text{k}\Omega$		<1	-20 -0.5	nA μA	$V_{CB} = -80\text{V}$ $V_{CB} = -80\text{V}$, $T_{amb} = 100^{\circ}\text{C}$
Emitter cut-off current	I_{EBO}		<1	-10	nA	$V_{EB} = -6\text{V}$
Collector-emitter saturation voltage	$V_{CE(SAT)}$		-14 -50 -80 -145	-20 -65 -115 -210	mV mV mV mV	$I_C = -0.1\text{A}$, $I_B = -10\text{mA}^*$ $I_C = -1\text{A}$, $I_B = -100\text{mA}^*$ $I_C = -2\text{A}$, $I_B = -200\text{mA}^*$ $I_C = -4\text{A}$, $I_B = -400\text{mA}^*$
Base-emitter saturation voltage	$V_{BE(SAT)}$		-960	-1060	mV	$I_C = -4\text{A}$, $I_B = -400\text{mA}^*$
Base-emitter turn-on voltage	$V_{BE(ON)}$		-850	-960	mV	$I_C = -4\text{A}$, $V_{CE} = -1\text{V}^*$
Static forward current transfer ratio	h_{FE}	100 100 65 10	250 200 120 25	300		$I_C = -10\text{mA}$, $V_{CE} = -1\text{V}^*$ $I_C = -1\text{A}$, $V_{CE} = -1\text{V}^*$ $I_C = -4\text{A}$, $V_{CE} = -1\text{V}^*$ $I_C = -10\text{A}$, $V_{CE} = -1\text{V}^*$
Transition frequency	f_T		120		MHz	$I_C = -100\text{mA}$, $V_{CE} = -10\text{V}$ $f = 50\text{MHz}$
Output capacitance	C_{OBO}		48		pF	$V_{CB} = -10\text{V}$, $f = 1\text{MHz}^*$
Switching times	t_{ON} t_{OFF}		39 370		ns	$I_C = -1\text{A}$, $V_{CC} = -10\text{V}$, $I_{B1} = I_{B2} = -100\text{mA}$

* Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

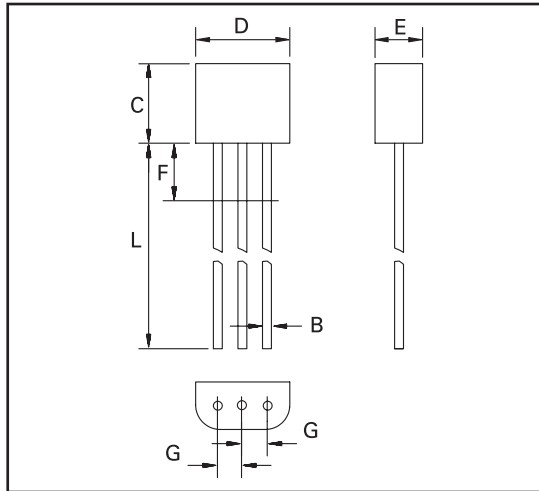
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TYPICAL CHARACTERISTICS



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PACKAGE OUTLINE



Controlling dimensions are in millimeters. Approximate conversions are given in inches

PACKAGE DIMENSIONS

DIM	Millimeters		Inches	
	Min	Max	Min	Max
A	0.41	0.495	0.016	0.0195
B	0.41	0.495	0.016	0.0195
C	3.61	4.01	0.142	0.158
D	4.37	4.77	0.172	0.188
E	2.16	2.41	0.085	0.095
F	—	2.50	—	0.098
G	1.27 NOM		0.050 NOM	
L	13.00	13.97	0.512	0.550

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